

ABSTRACT

A semiconductor failure analysis device 1 includes a first analysis unit 10 that emits first irradiation light L1 along a first path R1 set on a first main surface D1 of a semiconductor device D, a second analysis unit 20 that emits second irradiation light L2 along a second path R2 set on a second main surface D2 that is a back side of the first main surface D1, an electric signal acquisition unit 61 that receives an electric signal output from the semiconductor device D irradiated with the first irradiation light L1 and the second irradiation light L2, and a computer 40 that controls the second analysis unit 20. A size of a first irradiation region A1 formed on the first main surface D1 with the first irradiation light L1 is different from a size of a second irradiation region A2 formed on the second main surface D2 with the second irradiation light L2. The computer 40 emits the first irradiation light L1 and the second irradiation light L2 while a state where the entire second irradiation region A2 overlaps the first irradiation region A1 is maintained.

Fig. 3